

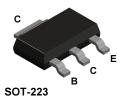
MPSA55

MMBTA55

PZTA55







PNP General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 73. See MPSA56 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	4.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic		Units		
		MPSA55	*MMBTA55	**PZTA55	
P _D	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

^{**}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	60		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I _E = 100 μA, I _C = 0	4.0		V
Iceo	Collector-Cutoff Current	V _{CE} = 60 V, I _B = 0		0.1	μΑ
Ісво	Collector-Cutoff Current	V _{CB} = 60 V, I _E = 0		0.1	μΑ

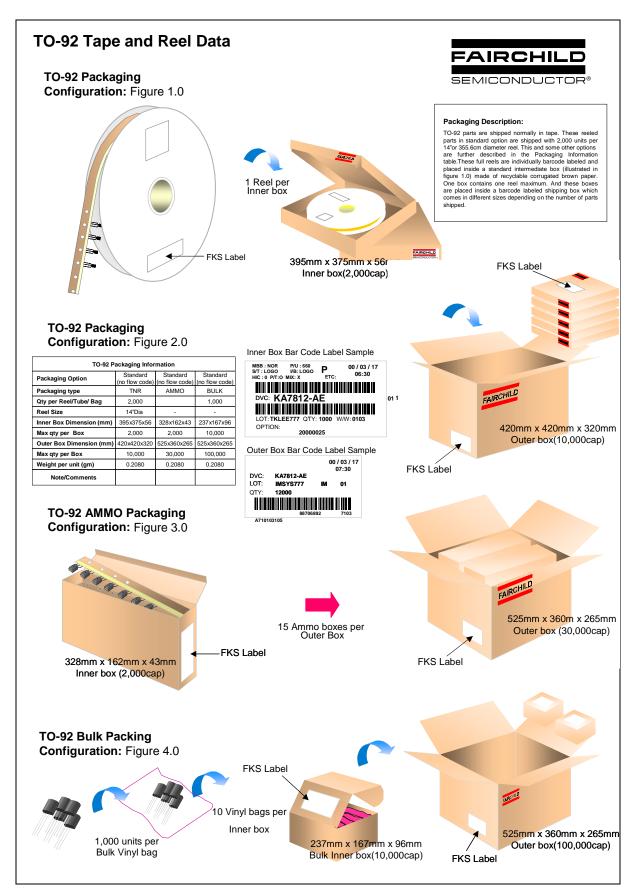
ON CHARACTERISTICS

h _{FE}	DC Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100 100		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.25	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 100 mA, V _{CE} = 1.0 V		1.2	V

SMALL SIGNAL CHARACTERISTICS

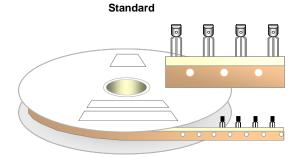
f _T	Current Gain - Bandwidth Product	$I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V},$	50	MHz
		f = 100 MHz		

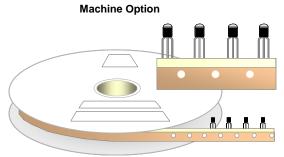
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%



TO-92 Tape and Reel Data, continued

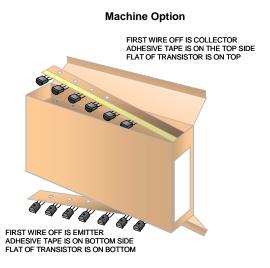
TO-92 Reeling Style Configuration: Figure 5.0

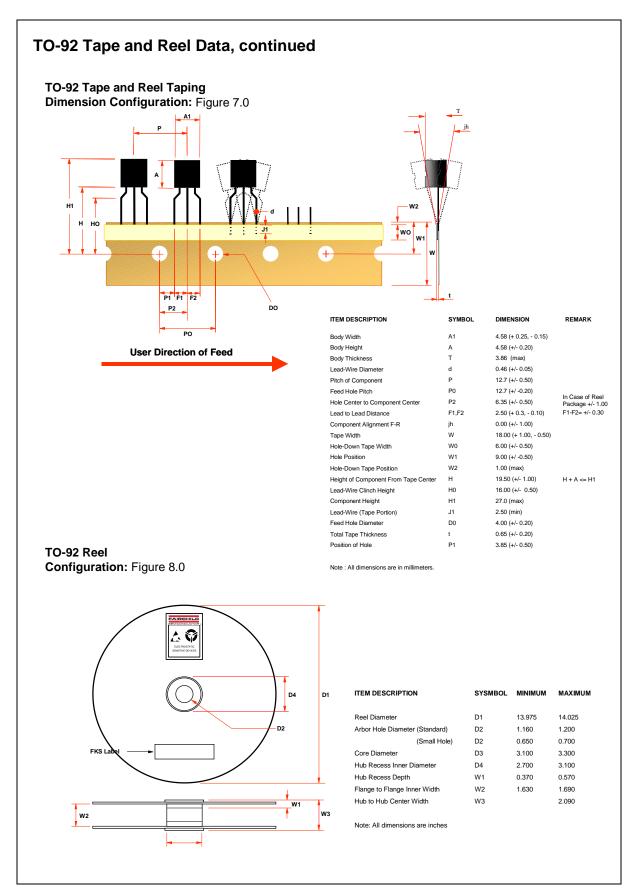


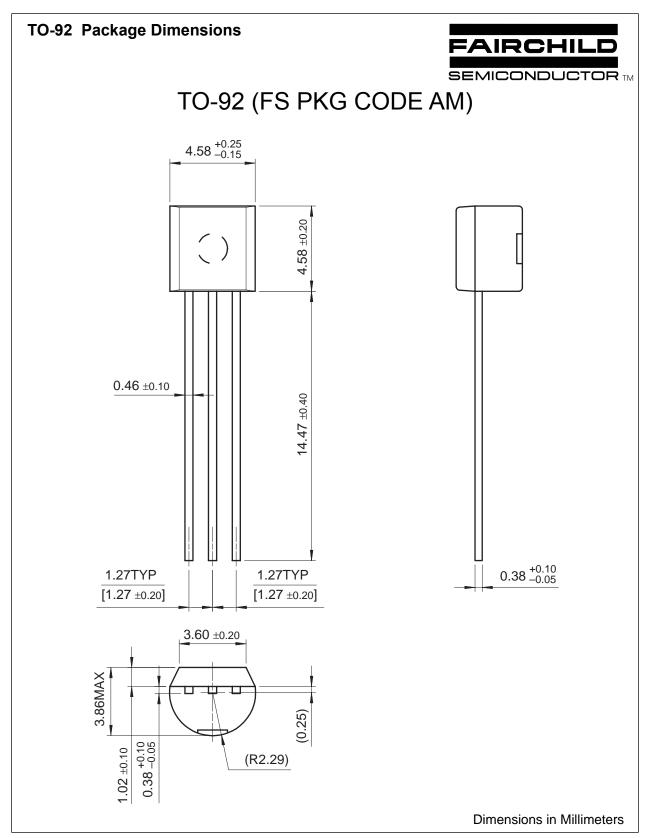


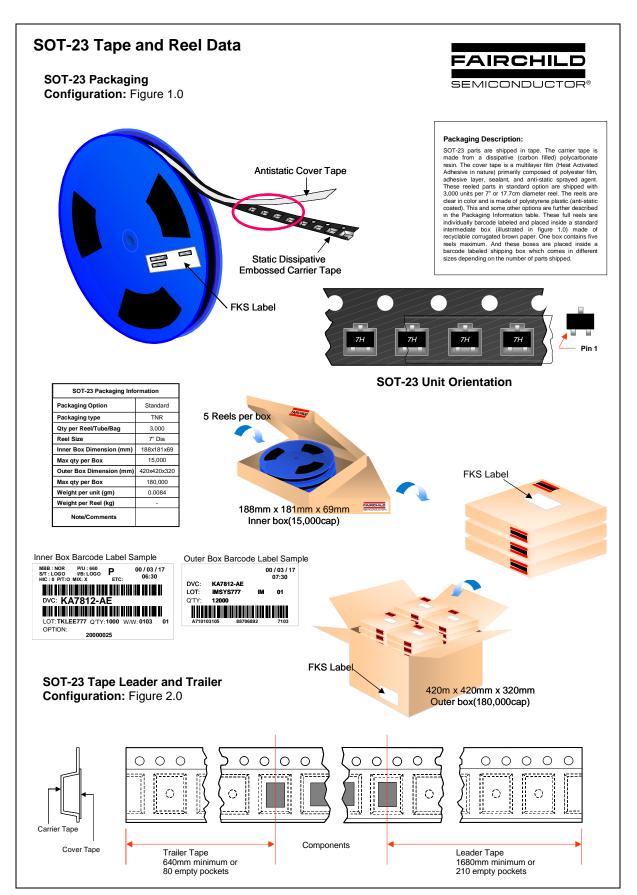
TO-92 Radial Ammo Packaging Configuration: Figure 6.0

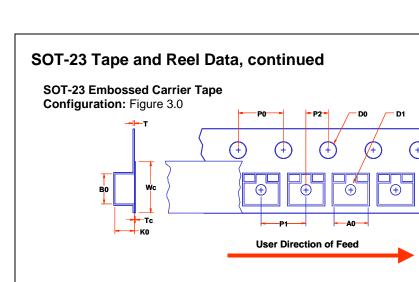
Standard FIRST WIRE OFF IS EMITTER ADHESIVE TAPE IS ON THE TOP SIDE FLAT OF TRANSISTOR IS ON BOTTOM FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP





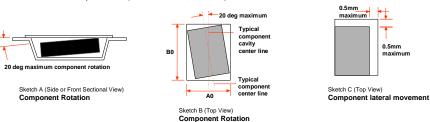






Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).

7" Diameter Option



SOT-23 Reel
Configuration: Figure 4.0

W1 Measured at Hub

Dim A

max

Dim Dim D

min

Dim D

M3

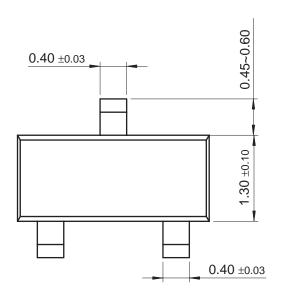
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8.0mm	7" Dia	7.00 177.8	0.059 1.5	0.512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

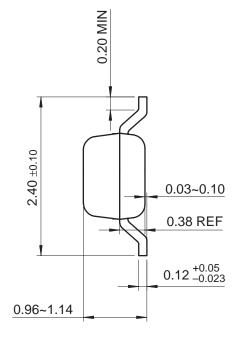
W2 max Measured at Hub

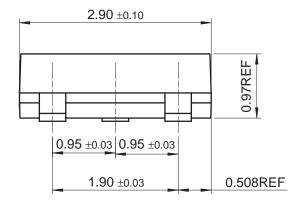
SOT-23 Package Dimensions



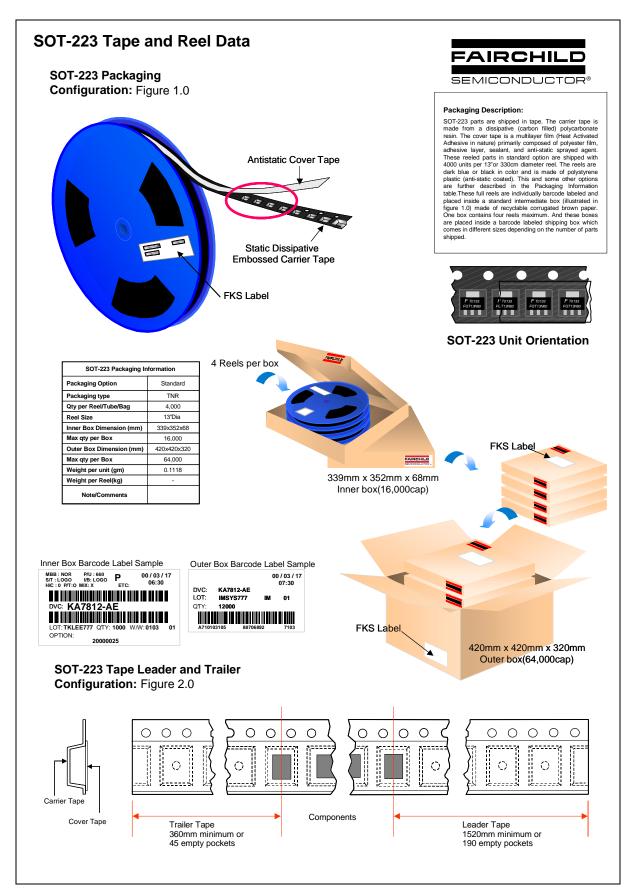
SOT-23 (FS PKG CODE AU)







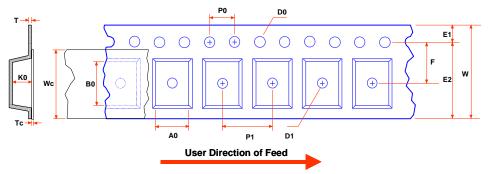
Dimensions in Millimeters





SOT-223 Embossed Carrier Tape

Configuration: Figure 3.0

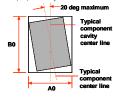


Dimensions are in millimeter														
Pkg type	A0	BO	w	D0	D1	E1	E2	F	P1	P0	KO	Т	Wc	Tc
SOT-223 (12mm)	6.83 +/-0.10	7.42 +/-0.10	12.0 +/-0.2	1.55 +/-0.05	1.50 +/-0.10	1.75 +/-0.10	10.25 min	5.50 +/-0.05	8.0 +/-0.1	4.0 +/-0.1	1.80 +/-0.10	0.30 +/-0.05	9.50 +/-0.1	0.10 max

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



Sketch B (Top View)
Component Rotation

W1 Measured at Hub

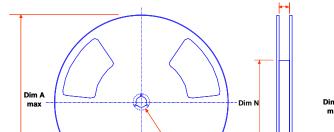


Sketch C (Top View)

Component lateral movement

SOT-223 Reel

Configuration: Figure 4.0





Dim C DETAIL AA

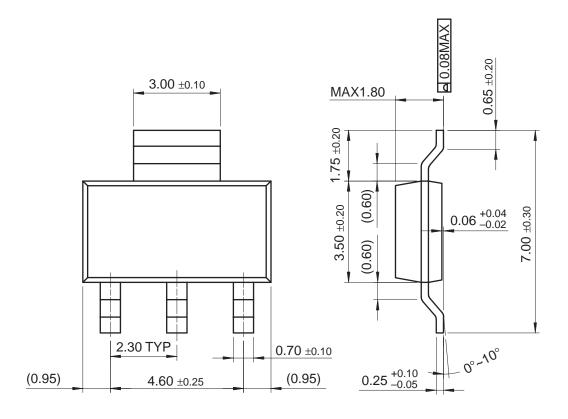
W2 max Measured at Hub

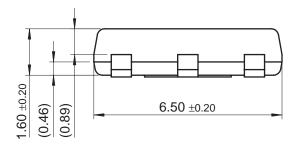
Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
12.0mm	13"Dia	13.00 330	0.059 1.5	0.512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.488 +0.078/-0.000 12.4 +2/0	0.724 18.4	0.468 -0.606 11.9 -15.4

SOT-223 Package Dimensions



SOT-223 (FS PKG CODE AV)





Dimensions in Millimeters

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